ABSTRACT

Provides an IC chip for high frequency region, particularly a packaged substrate in which no malfunction or error occurs even if 3GHz is exceeded.

Conductive layer 34P on core substrate 30 is formed in the thickness of 30μm and a conductor circuit 58 on interlayer resin insulation layer 50 is formed in the thickness of 15μm. By thickening the conductive layer 34P, the volume of the conductor can be increased and resistance can be reduced. Further, by using the conductive layer 34 as a power source layer, the capacity of supply of power to an IC chip can be improved.

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